

**Description**

The RST6020L uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

**General Features**

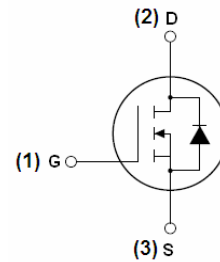
- $V_{DS} = 60V, I_D = 20A$   
 $R_{DS(ON)} < 44m\Omega @ V_{GS} = 10V$
- High density cell design for ultra low  $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

**Application**

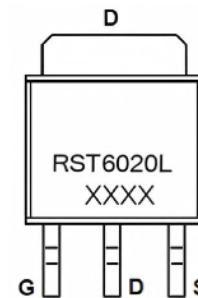
- Power management

**100% UIS TESTED!**

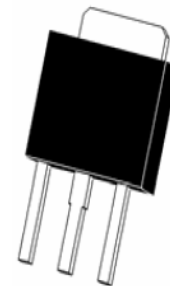
**100%  $\Delta V_{ds}$  TESTED!**



**Schematic diagram**



**Marking and pin assignment**



**TO-251S top view**

**Package Marking and Ordering Information**

| Device Marking | Device   | Device Package | Reel Size | Tape width | Quantity |
|----------------|----------|----------------|-----------|------------|----------|
| RST6020L       | RST6020L | TO-251S        | -         | -          | -        |

**Absolute Maximum Ratings ( $T_C = 25^\circ C$  unless otherwise noted)**

| Parameter                                         | Symbol              | Limit      | Unit          |
|---------------------------------------------------|---------------------|------------|---------------|
| Drain-Source Voltage                              | $V_{DS}$            | 60         | V             |
| Gate-Source Voltage                               | $V_{GS}$            | $\pm 20$   | V             |
| Drain Current-Continuous                          | $I_D$               | 20         | A             |
| Drain Current-Continuous( $T_C = 100^\circ C$ )   | $I_D (100^\circ C)$ | 14         | A             |
| Pulsed Drain Current                              | $I_{DM}$            | 45         | A             |
| Maximum Power Dissipation                         | $P_D$               | 30         | W             |
| Derating factor                                   |                     | 0.2        | W/ $^\circ C$ |
| Single pulse avalanche energy <sup>(Note 5)</sup> | $E_{AS}$            | 72         | mJ            |
| Operating Junction and Storage Temperature Range  | $T_J, T_{STG}$      | -55 To 175 | $^\circ C$    |

**Pb Free Product**
**Thermal Characteristic**

|                                                          |                 |   |                      |
|----------------------------------------------------------|-----------------|---|----------------------|
| Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup> | $R_{\theta JC}$ | 5 | $^{\circ}\text{C/W}$ |
|----------------------------------------------------------|-----------------|---|----------------------|

**Electrical Characteristics ( $T_C=25^{\circ}\text{C}$  unless otherwise noted)**

| Parameter                                     | Symbol              | Condition                                                                                                  | Min | Typ  | Max  | Unit |
|-----------------------------------------------|---------------------|------------------------------------------------------------------------------------------------------------|-----|------|------|------|
| Off Characteristics                           |                     |                                                                                                            |     |      |      |      |
| Drain-Source Breakdown Voltage                | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =250μA                                                                  | 60  | -    | -    | V    |
| Zero Gate Voltage Drain Current               | I <sub>DSS</sub>    | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V                                                                  | -   | -    | 1    | μA   |
| Gate-Body Leakage Current                     | I <sub>GSS</sub>    | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                                                                 | -   | -    | ±100 | nA   |
| On Characteristics <sup>(Note 3)</sup>        |                     |                                                                                                            |     |      |      |      |
| Gate Threshold Voltage                        | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA                                                   | 1.0 | 2.0  | 3.0  | V    |
| Drain-Source On-State Resistance              | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =10A                                                                  | -   | 37   | 44   | mΩ   |
| Forward Transconductance                      | g <sub>FS</sub>     | V <sub>DS</sub> =5V, I <sub>D</sub> =4.5A                                                                  | 11  | -    | -    | S    |
| Dynamic Characteristics <sup>(Note4)</sup>    |                     |                                                                                                            |     |      |      |      |
| Input Capacitance                             | C <sub>ISS</sub>    | V <sub>DS</sub> =30V, V <sub>GS</sub> =0V,<br>F=1.0MHz                                                     | -   | 500  | -    | PF   |
| Output Capacitance                            | C <sub>OSS</sub>    |                                                                                                            | -   | 60   | -    | PF   |
| Reverse Transfer Capacitance                  | C <sub>RSS</sub>    |                                                                                                            | -   | 25   | -    | PF   |
| Switching Characteristics <sup>(Note 4)</sup> |                     |                                                                                                            |     |      |      |      |
| Turn-on Delay Time                            | t <sub>d(on)</sub>  | V <sub>DD</sub> =30V, I <sub>D</sub> =2A, R <sub>L</sub> =6.7Ω<br>V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω | -   | 5    | -    | nS   |
| Turn-on Rise Time                             | t <sub>r</sub>      |                                                                                                            | -   | 2.6  | -    | nS   |
| Turn-Off Delay Time                           | t <sub>d(off)</sub> |                                                                                                            | -   | 16.1 | -    | nS   |
| Turn-Off Fall Time                            | t <sub>f</sub>      |                                                                                                            | -   | 2.3  | -    | nS   |
| Total Gate Charge                             | Q <sub>g</sub>      | V <sub>DS</sub> =30V, I <sub>D</sub> =4.5A,<br>V <sub>GS</sub> =10V                                        | -   | 14   |      | nC   |
| Gate-Source Charge                            | Q <sub>gs</sub>     |                                                                                                            | -   | 2.9  |      | nC   |
| Gate-Drain Charge                             | Q <sub>gd</sub>     |                                                                                                            | -   | 5.2  |      | nC   |
| Drain-Source Diode Characteristics            |                     |                                                                                                            |     |      |      |      |
| Diode Forward Voltage <sup>(Note 3)</sup>     | V <sub>SD</sub>     | V <sub>GS</sub> =0V, I <sub>S</sub> =20A                                                                   | -   |      | 1.2  | V    |
| Diode Forward Current <sup>(Note 2)</sup>     | I <sub>S</sub>      |                                                                                                            | -   | -    | 20   | A    |
| Reverse Recovery Time                         | t <sub>rr</sub>     | T <sub>J</sub> = 25°C, I <sub>F</sub> =20A<br>di/dt = 100A/μs <sup>(Note3)</sup>                           | -   | 35   | -    | nS   |
| Reverse Recovery Charge                       | Q <sub>rr</sub>     |                                                                                                            | -   | 53   | -    | nC   |
| Forward Turn-On Time                          | t <sub>on</sub>     | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)                                       |     |      |      |      |

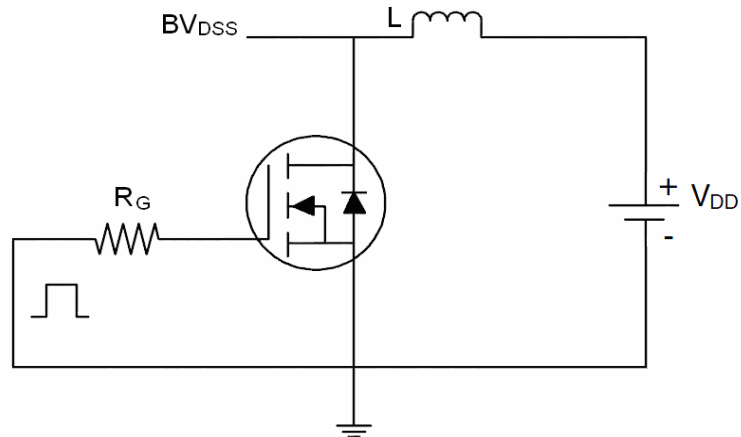
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, L=0.1\text{mH}, R_g=25\Omega$

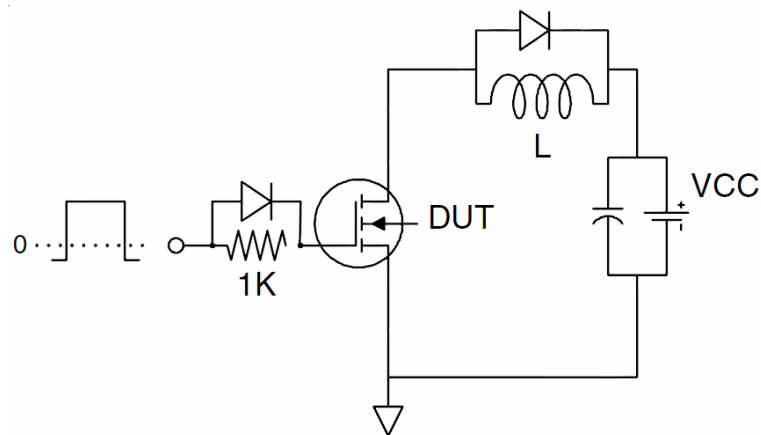
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### Test Circuit

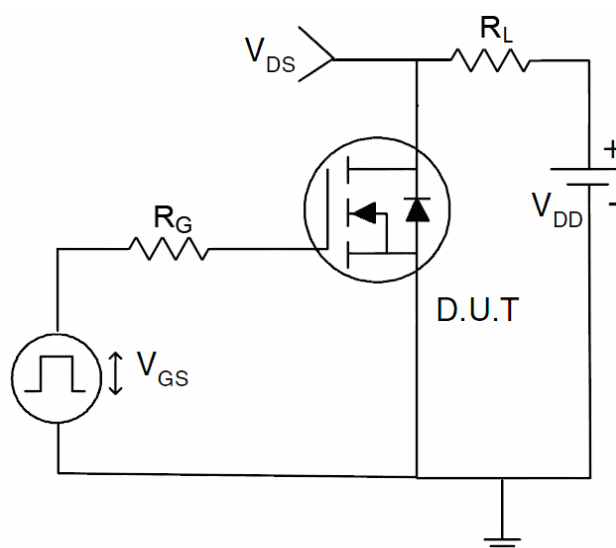
#### 1) $E_{AS}$ test Circuit

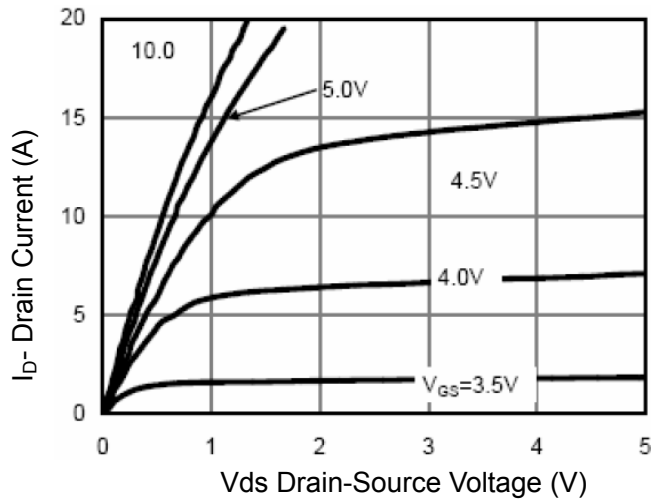
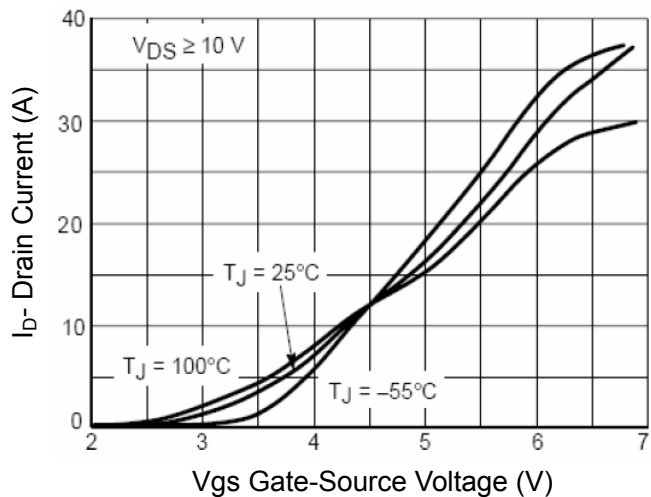
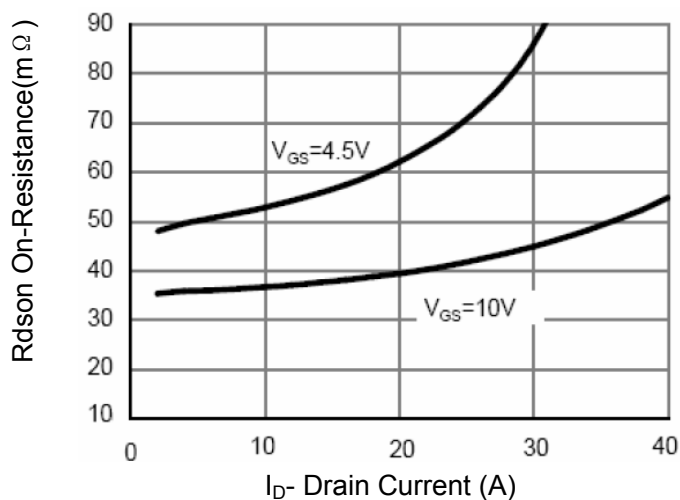
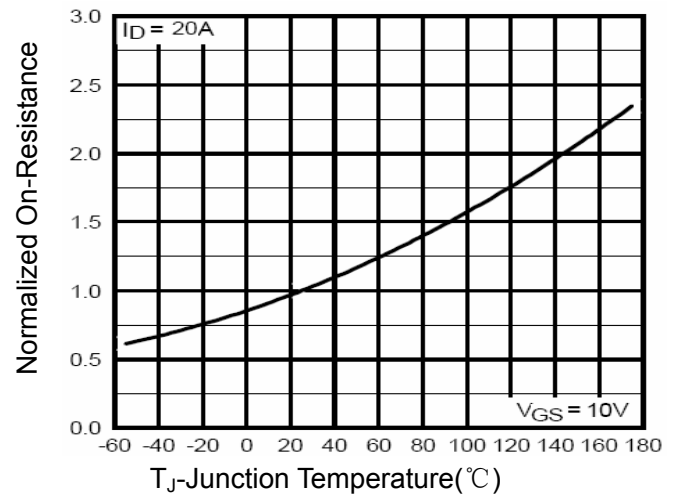
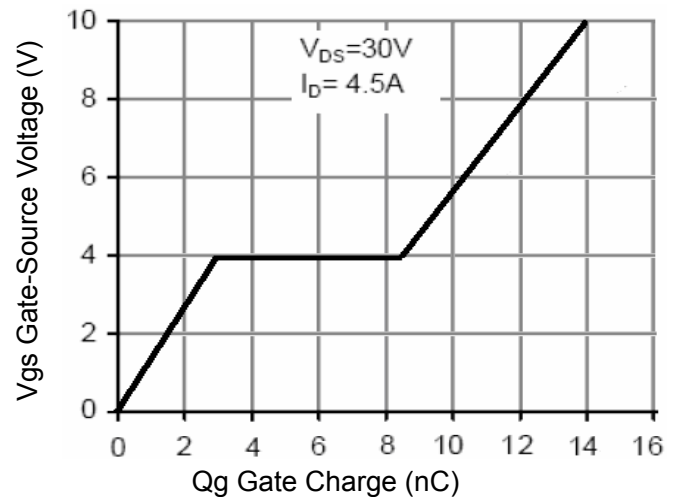
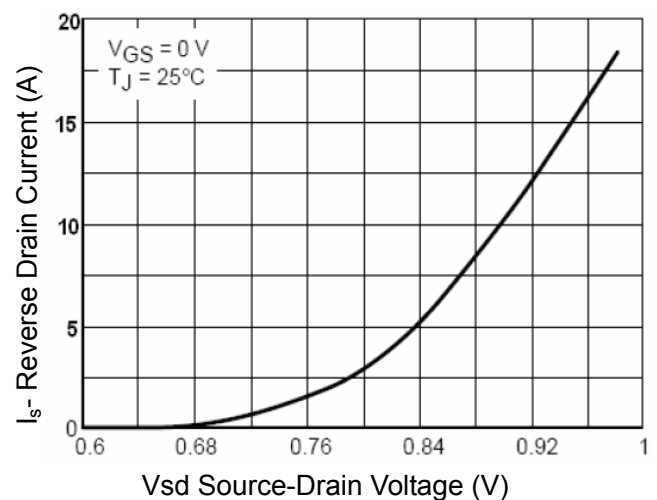


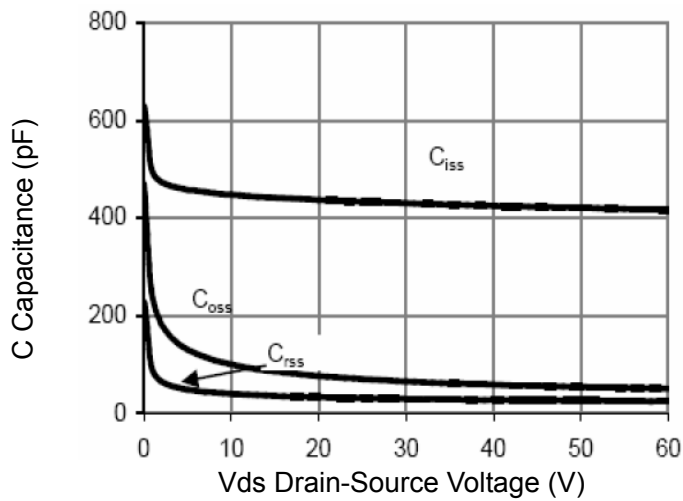
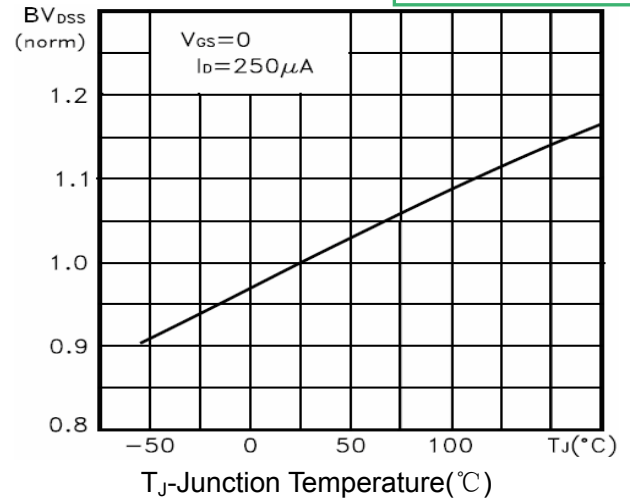
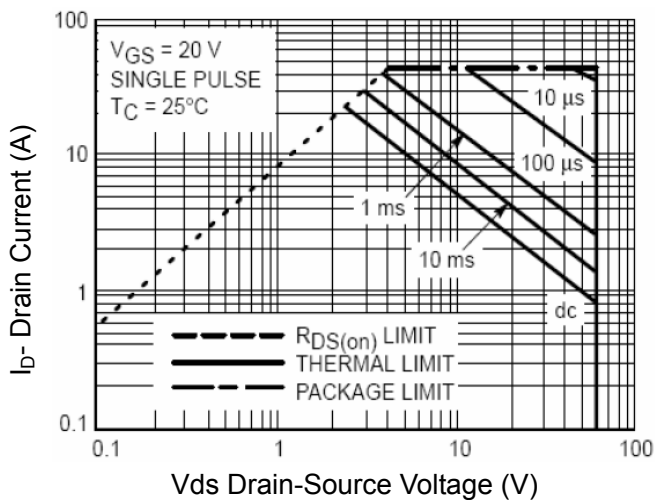
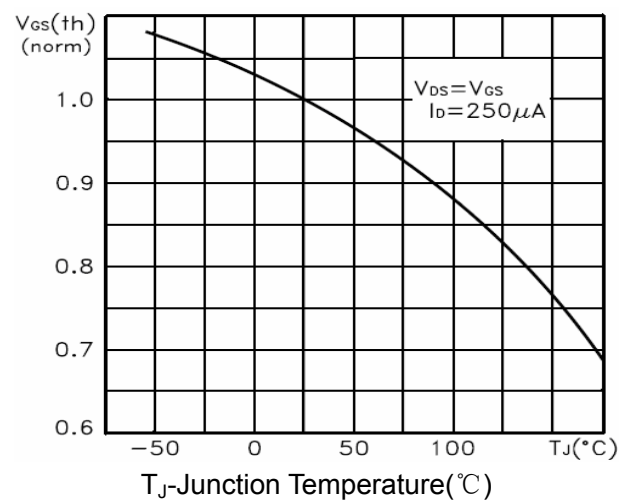
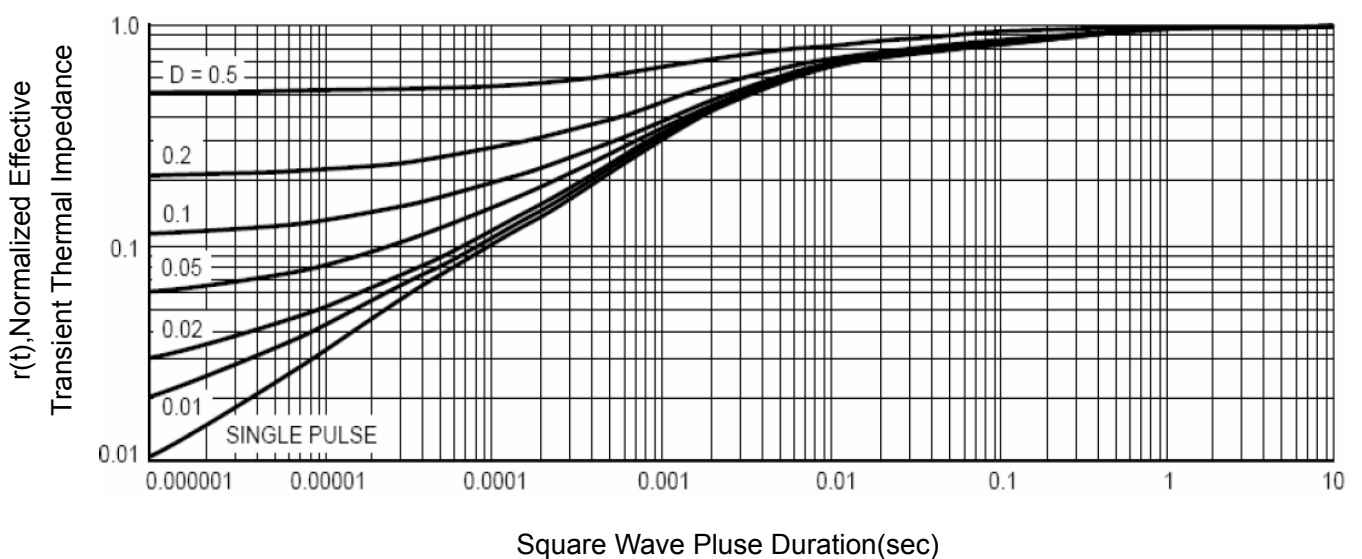
#### 2) Gate charge test Circuit

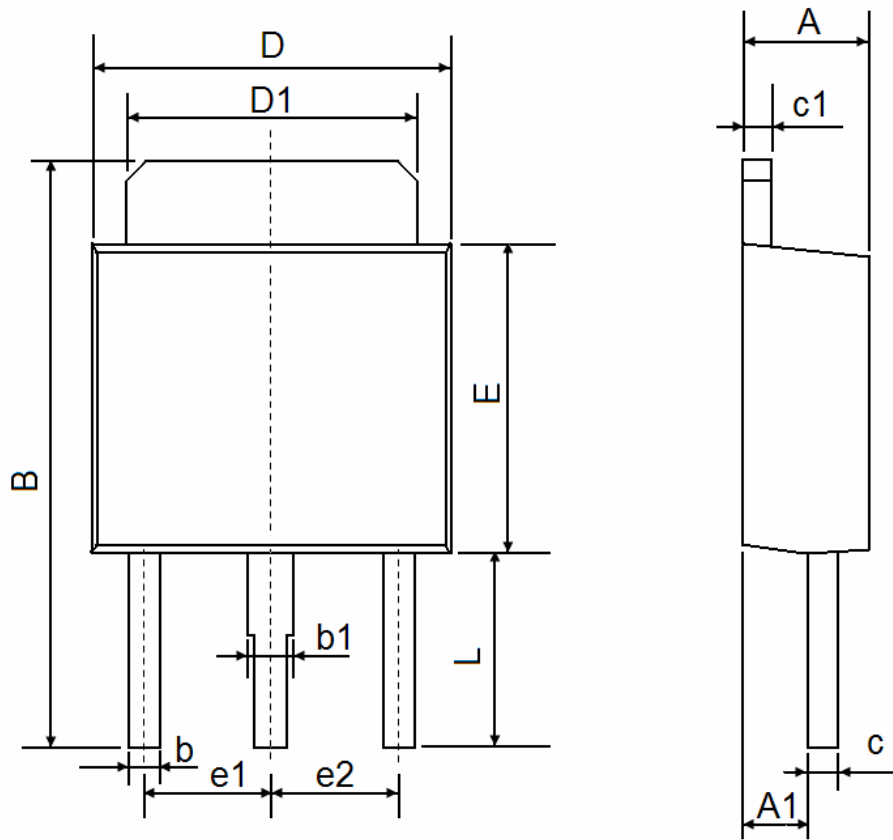


#### 3) Switch Time Test Circuit



**Typical Electrical and Thermal Characteristics (Curves)**
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**Figure 1 Output Characteristics**

**Figure 2 Transfer Characteristics**

**Figure 3 Rdson- Drain Current**

**Figure 4 Rdson-Junction Temperature**

**Figure 5 Gate Charge**

**Figure 6 Source- Drain Diode Forward**

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**Figure 7 Capacitance vs Vds**

**Figure 9  $BV_{DSS}$  vs Junction Temperature**

**Figure 8 Safe Operation Area**

**Figure 10  $V_{GS(th)}$  vs Junction Temperature**

**Figure 11 Normalized Maximum Transient Thermal Impedance**

**TO-251S Package Information**
**Pb Free Product**


| Symbol | Dimensions In Millimeters |        | Dimensions In Inches |       |
|--------|---------------------------|--------|----------------------|-------|
|        | Min.                      | Max.   | Min.                 | Max.  |
| A      | 2.250                     | 2.350  | 0.089                | 0.093 |
| A1     | 1.150                     | 1.250  | 0.045                | 0.049 |
| B      | 10.200                    | 10.800 | 0.402                | 0.425 |
| b      | 0.550                     | 0.650  | 0.022                | 0.026 |
| b1     | 0.750                     | 0.850  | 0.030                | 0.033 |
| c      | 0.480                     | 0.540  | 0.019                | 0.021 |
| c1     | 0.480                     | 0.540  | 0.019                | 0.021 |
| D      | 6.400                     | 6.600  | 0.252                | 0.260 |
| D1     | 5.250                     | 5.350  | 0.207                | 0.211 |
| E      | 5.400                     | 5.600  | 0.213                | 0.220 |
| e1     | 2.300 TYP                 |        | 0.091 TYP            |       |
| e2     | 2.300 TYP                 |        | 0.091 TYP            |       |
| L      | 3.300                     | 3.700  | 0.130                | 0.146 |